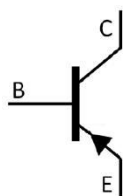


SOT-323 PNP Silicon PNP transistor in a SOT-323 Plastic Package.

2SC1741W

Large I_c low $V_{ce(sat)}$, complementary pair with the 2SC1741W.

Medium power amplifier applications.

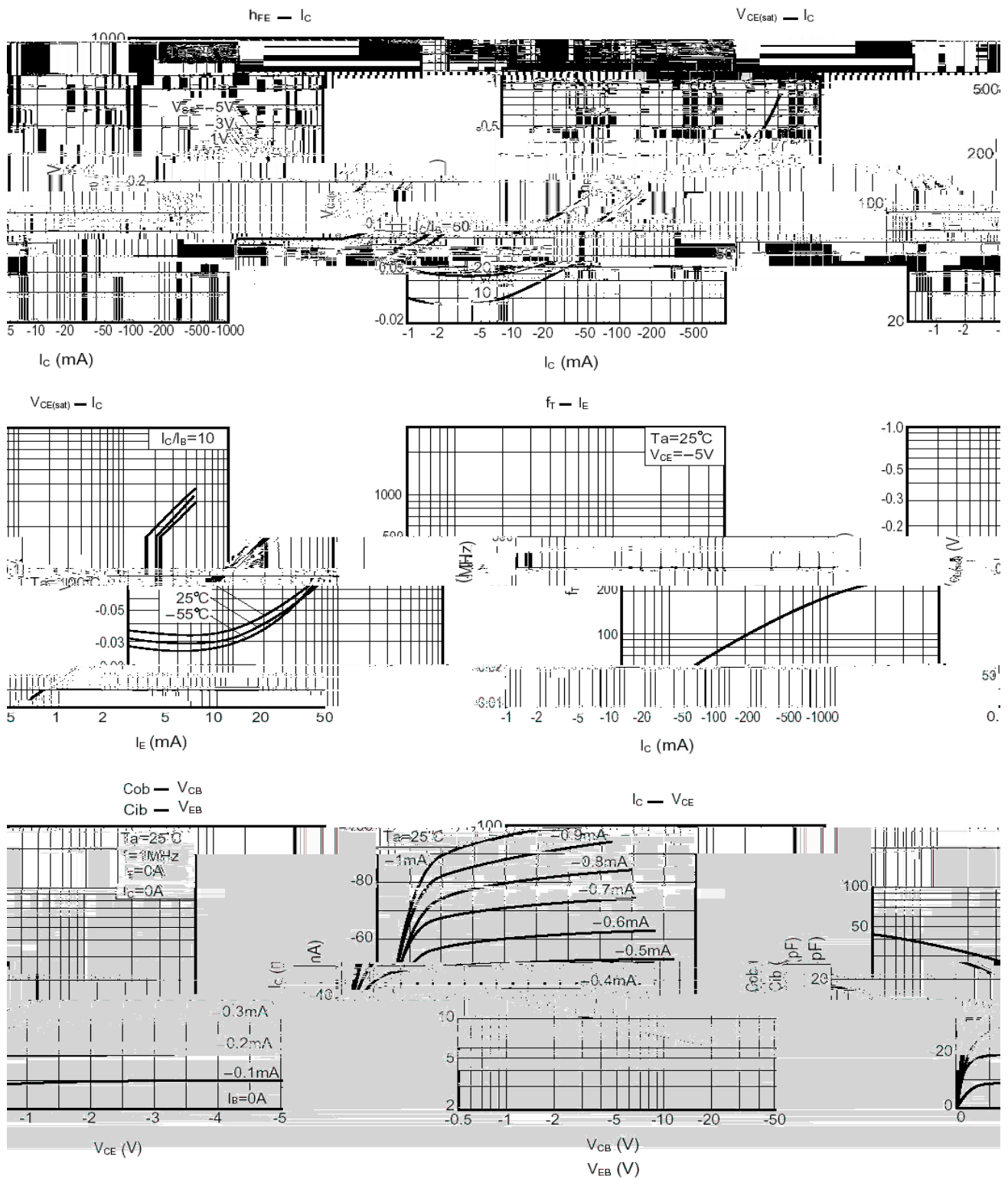


PIN1 Emitter PIN 2 Base PIN 3 Collector

h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82 180	120 270	180 390
Marking	HHP	HHQ	HHR

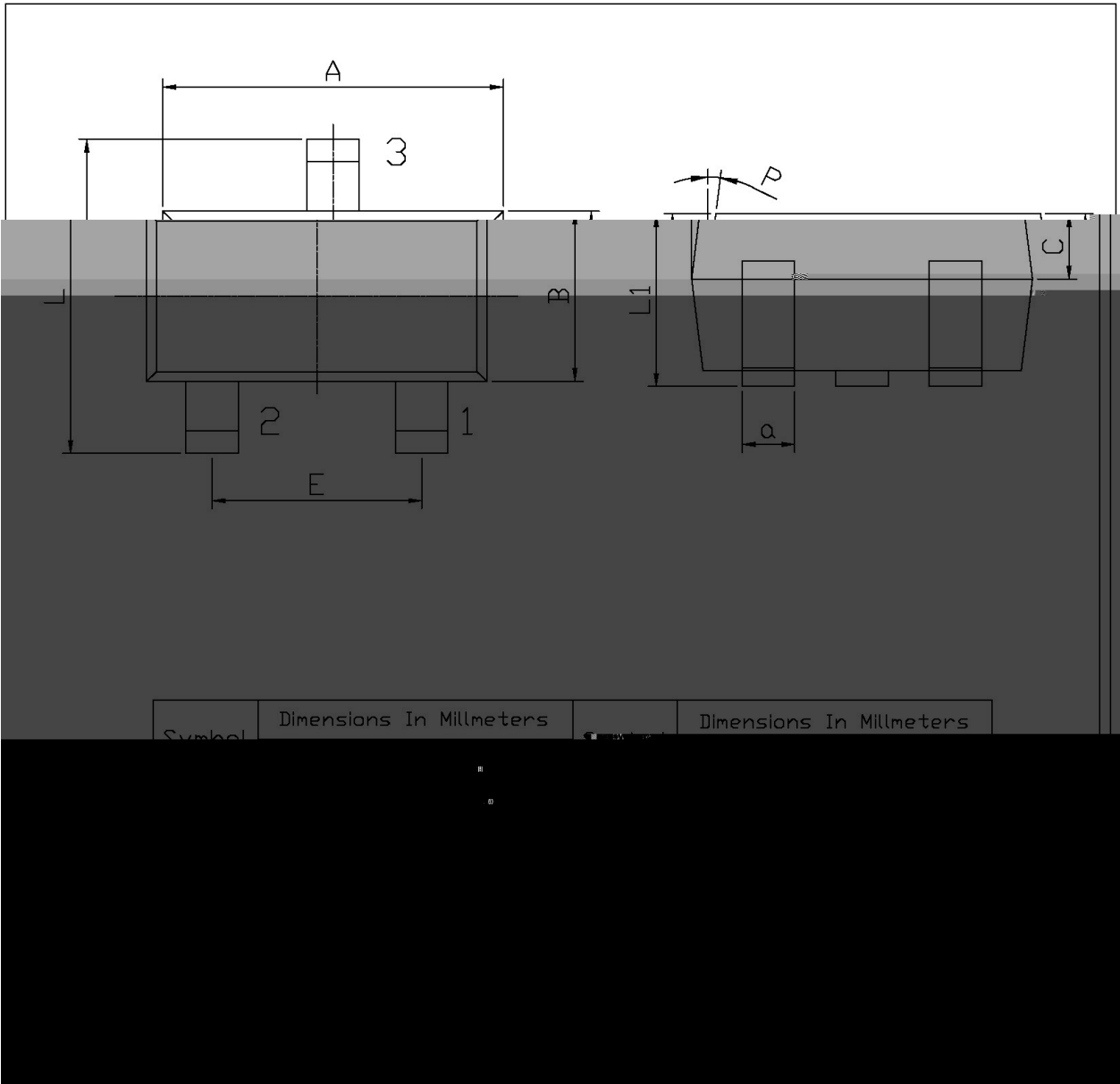
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-40	V
Collector to Emitter Voltage	V_{CEO}	-32	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-500	mA
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

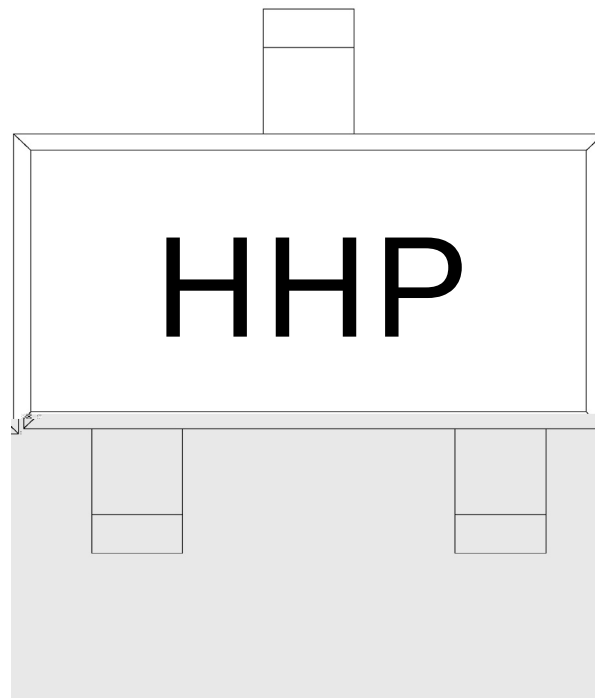
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C = -100\mu A$	-40			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C = -1.0mA$	-32			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E = -100\mu A$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB} = -20V$			-1.0	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB} = -4.0V$			-1.0	μA
DC Current Gain	h_{FE}	$V_{CE} = -3.0V$ $I_C = -10mA$	82		390	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = -100mA$ $I_B = -10mA$			-0.4	V
Transition Frequency	f_T	$V_{CE} = -5.0V$ $f = 100MHz$ $I_E = 20mA$		200		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10V$ $f = 1.0MHz$ $I_E = 0$		7.0		pF



SOT-323

单位：mm





H

H

P h_{FE}

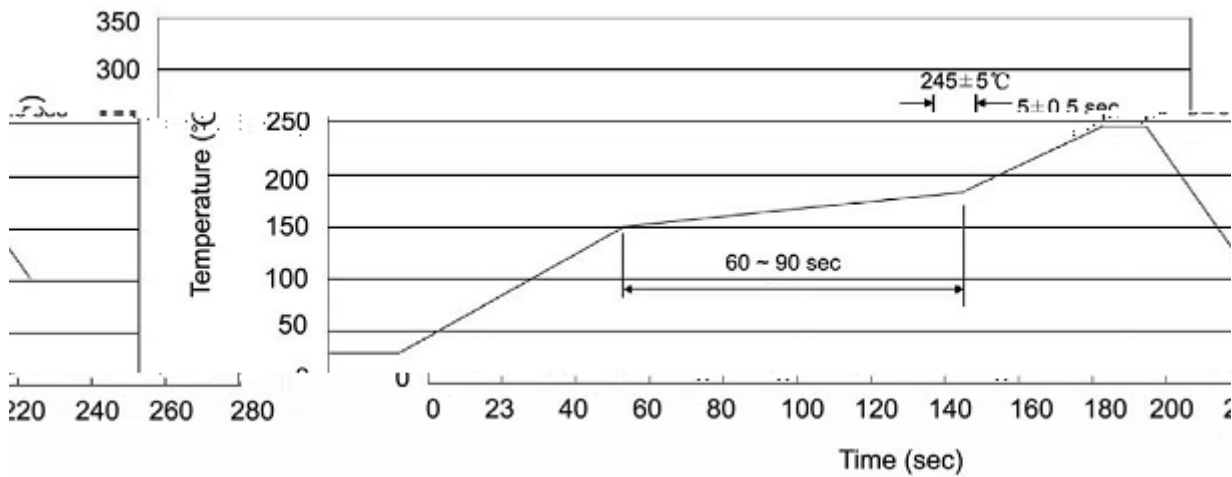
Note:

H: Company Code.

H: Product Type.

P h_{FE} Classifications Symbol

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;

1.Preheating:25~150 , Time:60~90sec.
- 2

245±5

5±0.5sec;

2.Peak Temp.:245±5 , Duration:5±0.5sec.
- 3

2 10 /sec.

3. Cooling Speed: 2~10 /sec.

260±5

10±1 sec.

Temp.:260±5

Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱